Lect. 5: PN Junction Diode (Razavi 2.2, 3.1)







Do currents flow when two terminals are shorted?



Diffusion of holes (P to N) and electrons (N to P)

 \rightarrow Diffusion currents (due to diffusion) to the right







Diffusion causes depletion of carriers→ depletion region

Depletion layer provides built-in E-field

Built-in E-field produces drift current

$$I_{\text{total}} = I_{\text{diffusion}} + I_{\text{drift}} = 0$$

No currents due to balance between diffusion and drift currents



With bias voltage,

Balance between diffusion and drift currents is broken.

V>0: Forward Bias

- $|_{diffusion} >> |_{drift}$
- ➔ I_D>0, very large currents if V is sufficiently large

V<0: Reverse Bias

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 $|_{diffusion} < |_{drift}$

➔ I_D<0, but very little currents until breakdow





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With more detailed analyses



$$i = I_{S}[\exp(\frac{v}{V_{T}}) - 1]$$
$$(v > -V_{BD})$$

 I_s : saturation current usually very small

$$V_T$$
: thermal voltage
(= $\frac{kT}{q} \sim 25$ mV at Room Temp.)

V_{BD}: Breakdown voltage



Diode circuit analysis



What are v_D , $i_{D,}$, v_O as function of v_I ?



Node analysis: 3 unknows



$$v_{I} - v_{D} - v_{O} = 0$$
$$v_{O} = i_{D} \cdot R$$
$$i_{D} = I_{S} [\exp(\frac{v_{D}}{V_{T}}) - 1]$$

(Assume V_{BD} is very large)



Computers can \rightarrow SPICE

Electronic Circuits 1 (09/2)



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Graphical analysis (load line analysis)



Electronic Circuits 1 (09/2)





If $i_D > 0$ (Diode On), $v_D = 0$ (short) If $v_D < 0$ (Diode Off), $i_D = 0$ (open)

➔ Ideal diode model







If $i_D > 0$ (Diode On), $v_D = 0$ (short) If $v_D < 0$ (Diode Off), $i_D = 0$ (open)

Determine I, V using the ideal diode model





If $i_D > 0$ (Diode On), $v_D = 0$ (short) If $v_D < 0$ (Diode Off), $i_D = 0$ (open)





Homework (Due on 9/14 before tutorial):

- Prob. 3.9 in Razabi

